# **FTM simulations**

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# Procedure

- ANSYS and Garfield++ codes fully automatic. Just needs to change nlayer.
- Analysis for 1, 4, 8, 12, 16 layers: amp field 100kV/cm, drift field 3kV/cm
- Ar/CO2 70:30, penning at 0.57
- 150 GeV/c Muon track in Garfield++ using HEED class
- For each layer, we record the gain: charge liberated, given by the total number of electrons created in the avalanche and arriving on the PCB
- For each layer, we record the time of the electron created in the avalanche and the time of arrival on PCB
- For each layer, we keep the minimum of the timing, giving the resolution the detector









0

-100

-200

-300

-400

-500

-600



#### **Garfield++ Field View**



150 GeV/c muon in 4-layer FTM



**Timing histograms in 4 layers** 



**Orange: Amplification time, Blue: endpoint time** 

All 4 layers together



## 150 GeV/c muon in 8-layer FTM



19511 0.956 0.735 0

> 2.5 Time (ns)

17611 2.81 0.296

4226 0.432 0.274 0

**Orange:** Amplification time, **Blue**: endpoint time

# **Timing histograms in 8 layers**



All layers together



#### Summary

- Example of time resolution for 8-layer FTM (~ 450 ps)
- The mean value of each layer from the previous histograms is kept
- Entire Procedure is to be verified
- Gain (using track or electron? Total number?)
- 12 layers and 16 layers seems to have small problem with voltage
- Next steps?